



PRODUCT/PROCESS CHANGE NOTIFICATION

PCN MMS-MMY/07/3302
Notification Date 12/26/2007

M95256, 256Kbit Serial SPI Bus EEPROM Upgrade and Die Optimization

MMY - MEMORY

Table 1. Change Implementation Schedule

Forecasted implementation date for change	04-Jan-2008
Forecasted availability date of samples for customer	18-Jan-2008
Forecasted date for STMicroelectronics change Qualification Plan results availability	18-Jan-2008
Estimated date of changed product first shipment	26-Mar-2008

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	M95256 products family
Type of change	Product design change
Reason for change	Increase performance
Description of the change	Metal 1 mask
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	Process and fab ID see marking above
Manufacturing Location(s)	

Table 3. List of Attachments

Customer Part numbers list	
Qualification Plan results	



Customer Acknowledgement of Receipt		PCN MMS-MMY/07/3302
Please sign and return to STMicroelectronics Sales Office		Notification Date 12/26/2007
<input type="checkbox"/> Qualification Plan Denied	Name:	
<input type="checkbox"/> Qualification Plan Approved	Title:	
	Company:	
<input type="checkbox"/> Change Denied	Date:	
<input type="checkbox"/> Change Approved	Signature:	
Remark		
.....		
.....		
.....		
.....		
.....		
.....		
.....		
.....		
.....		
.....		
.....		
.....		

DOCUMENT APPROVAL

Name	Function
Leduc, Hubert	Division Marketing Manager
Rodrigues, Benoit	Division Product Manager
Yackowlew, Nicolas	Division Q.A. Manager



**M95256, 256Kbit Serial SPI Bus EEPROM
Upgrade and Die Optimization**

What is the change?

The M95256, 256Kbit Serial SPI Bus EEPROM product family, will undergo a design change: a metal 1 mask change will allow a better trimming of the programming voltage, it will improve the product programmability and endurance over the full Automotive grade temperature (-40°C / 150°C).

As part of ST commitment to continuous improvement, this design change will be implemented for the whole production.

Why?

The strategy of STMicroelectronics Memory Division is to support the growth of our customers on a long-term basis. In line with this commitment, the qualification of the redesigned M95256 will allow to serve new markets requiring high endurance at high temperature as well as applications in industrial range with a single product design.

When?

The production of the upgraded M95256 in the ST Rousset (France) 8 inch wafer diffusion plant will ramp up from January 2008 and shipments will start from March 2008 onward.

How will the change be qualified?

The new version of the M95256 will be qualified using the standard ST Microelectronics Corporate Procedures for Quality and Reliability.

The qualification report QREE0522 will be updated (rev 06) and will be available on Week 03 / 2008.

Note: a similar design solution was already qualified in the M95512 from same process.

What is the impact of the change?

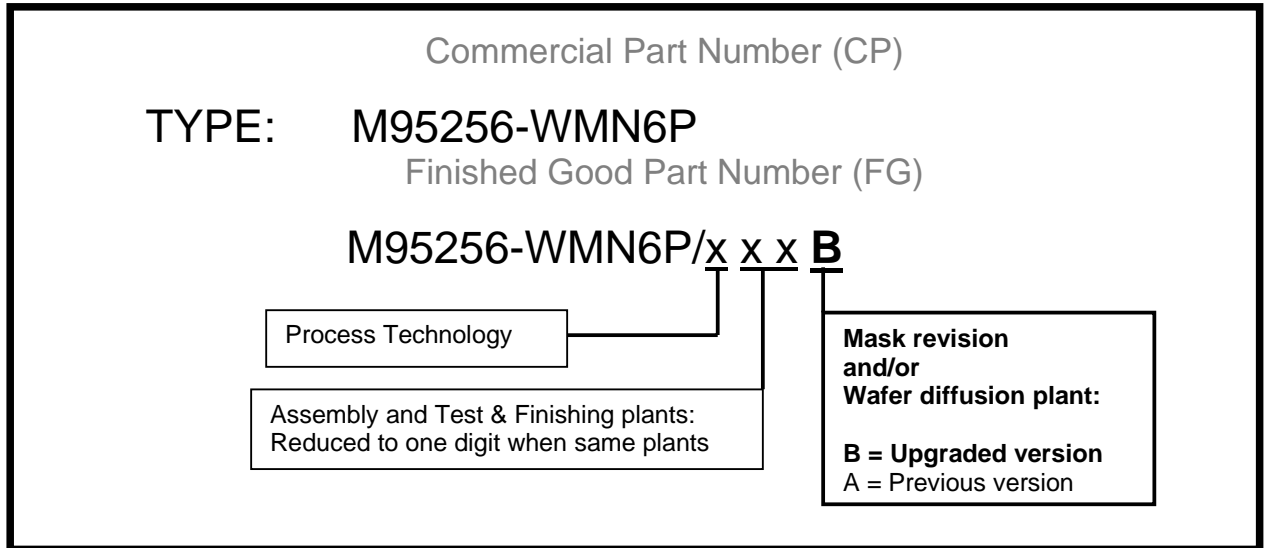
- **Form:** marking change (see **Device marking** paragraph)
- **Fit:** no change
- **Function:** Higher endurance over the full Automotive grade temperature range (-40°C / 150°C). The Datasheet remains identical.

How can the change be seen?

- BOX LABEL MARKING

On the BOX LABEL MARKING, the change is visible inside the Finished Good Part Number: the **Mask revision and /or Wafer diffusion plant** identifier is “**B**” for the **upgraded version in SO8N**, this identifier being “**A**” for the previous version.

→ Example for M95256-WMN6P (2.5V to 5.5V Vcc range, SO8N RoHS* compliant package)



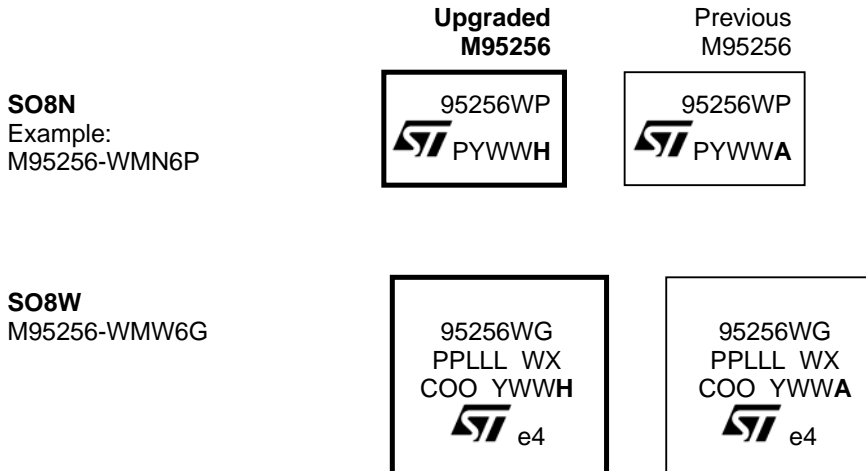
*RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipments

How can the change be seen?

- DEVICE MARKING

On the DEVICE MARKING of the **SO8N** package, the change is visible inside the trace code (PYWWT) where the last digit “T” for **Process Technology** identifier is “H” for the **upgraded version**, the identifier being “A” for the previous version.

On the DEVICE MARKING of the **SO8W**, the change is visible inside the second line of the trace code (YWWT) where the last digit “T” for **Process Technology** identifier is “H” for the **upgraded version**, the identifier being “A” for the previous version.



The traceability for each device is as follows:

P or PP Y WW LLL WX T

P(PP) = Assembly country & plant
 Y = Last digit of the Year of Assembly
 WW = Assembly Week code
 LLL = chronological sequence
 WX = Wafer diffusion plant
 COO = Country of origin (Assembly)
T = Process Technology code/ Wafer Fab ID

For **TSSOP8** package size reason, the change is not visible on the device marking. The change is only visible inside the Finished Good Part Number appearing on the BOX LABEL MARKING (see previous page).

Appendix A- Product Change Information

Product family / Commercial products:	M95256 products family
Customer(s):	All
Type of change:	Design refine
Reason for the change:	Increase performance
Description of the change:	Metal 1 mask
Forecast date of the change:	January 2008
Forecast availability date of qualification sample for the customer(s):	Week 03 / 2008
Forecast date for the internal STMicroelectronics change, Qualification report availability:	Week 03 / 2008
Marking to identify the changed product:	Process and fab ID see marking above
Description of the qualification program:	Standard ST Microelectronics Corporate Procedures for Quality and Reliability
Product Line(s) and/or Part Number(s):	See list of concerned products in appendix B
Manufacturing location:	Rousset 8 inch wafer fab
Estimated date of first shipment:	March 2008
Division Product Manager: B. RODRIGUES	Date:
Group QA Manager: N. YACKOWLEW	Date:

Appendix B: concerned products:

M95256-WMN6P
M95256-WMN6TP
M95256-WDW6TP
M95256-WMW6G
M95256-WMW6TG
M95256-RMN6P
M95256-RMN6TP
M95256-RDW6TP

Appendix C: Qualification Plan:**M95256 Redesigned version B**Using **CMOSF8L** silicon process technology in **R8** Fab**PRODUCT DESCRIPTION**

	Device to qualify	Qualified similar device
Product name	M95256 Redesigned version B	M95512 / M24512
Memory size	256K	512K
Bus protocol	SPI	SPI
Process	CMOSF8L / R8	CMOSF8L / R8

SIMILARITY

The new metal mask was already qualified on the 512K SPI and I2C products (respectively QREE0703 and QREE0719).

According to STMicroelectronics specifications 0068577 and SOP2.6.14, the qualification activities were planned on 1 lot for die-oriented trials.

CHARACTERIZATION**Table 1. Characterization requirements.**

Number of lots	Parameters	Vcc range	Temperature range
1	All	1.8V/5.5V	-40°C/150°C

RELIABILITY TEST PLAN**Table 2. Die-oriented reliability test plan and results summary**

Test	Test short description					
	Method	Conditions	Sample size / lots	Number of lots	Duration	Results fail / sample size
EDR (HTOL after W/E)	High temperature operating life after endurance					
	AEC-Q100-005 JESD22-A108	1Mcy W/E @ 25°C then: HTOL 150°C / 1.2xVcc max (6V)	80	1	1008 hours	0/80
EDR (Bake after W/E)	Data retention after endurance					
	AEC-Q100-005 JESD22-A103	1Mcy W/E @ 25°C then: Retention Bake at 150°C Retention field = Checkerboard	80	1	1008 hours	0/80
LTOL	Low temperature operating life					
	JEDEC JESD22-A108	-40°C / 1.2xVcc max (6V)	80	1	1008 hours	0/80
HTSL	High temperature storage life					
	AEC-Q100-005 JESD22-A103	200°C / No bias Retention field = Checkerboard	80	1	1008 hours	0/80
WEB	Program/Erase endurance cycling + bake					
	Internal spec.	Cycling at 25°C / Vcc max then: Retention Bake at 200°C / 48 hours Retention field = Checkerboard	80	1	1000Kcycles / 48 hours	0/80 ⁽¹⁾
ESD (HBM)	Electro static discharge (human body model)					
	AEC-Q100-002 JESD22-A114	C = 100 pF, R = 1500 Ohms	27	1	N/A	Pass > 4000V
ESD (MM)	Electro static discharge (machine model)					
	AEC-Q100-003 JESD22-A115	C = 200 pF, R = 0 Ohms	9	1	N/A	Pass > 400V
LU	Latch-up (current injection and overvoltage stress)					
	AEC-Q100-004 JESD78A	At maximum operating temperature (150°C)	6	1	N/A	Class II - Level A

1. First rejects after 10 million cycles + Bake.

Document Revision History		
Date	Rev.	Description of the Revision
Oct. 01, 2007	1.00	First draft creation

Source Documents & Reference Documents		
Source document Title	Rev.:	Date:

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2007 STMicroelectronics - All rights reserved.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

